KISAB

Product specifications

Silicon carbide substrate material specification	
Property	**Value**
Polytype	4H polytype
Orientation	4˚ offcut
Diameter	200 ±0.05mm
Thickness	350+/- 10µm
Warp	<25µm
TTV	<4 µm
Surface treatment (Si-face)	Epi-ready
Resistivity	19.5-20.5 mΩ.cm
Resistivity uniformity	<2%
Edge exclusion	3 mm

Defect density	
Property	**Value**
Micropipes (MP)	<10 on wafer
Basal plane dislocation density (BPD)	<100 on wafer
Threading dislocation density (TD)	<1’400 cm^{-2}
Etch pit density (EPD)	<1’500 cm^{-2}

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